

Thermo-Mechanical Optimisation of Press Pack IGBT Packaging using Finite Element Method Simulation

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Introduction

Stages of Press Pack Optimisation

Design of Press Pack IGBT packaging needs to take into consideration of a number of requirements:



1. Protection of the IGBT structure

- 2. Minimisation of bulk stress in the IGBT
- 3. Minimisation of thermal resistance
- 4. Maximisation of compliance
- 5. Maximisation of reliability

These represent chip, cassette and package level requirements.

Chip Level Optimisation

- Microscopic defects on components reduces electrical performance, and can lead to failure of the chip
- Introducing a softer buffer between the molybdenum and IGBT emitter improves both yield and electrical performance



- 2D axisymmetric FEM simulation of defect indentation demonstrates how localised stresses may be redistributed.
- Buffer material has higher CTE than Silicon IGBT and Molybdenum Strain Buffer which may affect reliability
- kWL • Sliding distance used as metric for wear rate 0 = \overline{H} from Archards equation
- 3D Transient thermal-structural FEM highlights how the sliding distance across the emitter surface changes with increasing buffer layer thickness.
- The trade off between IGBT surface protection, which correlates to switching performance, and reliability is demonstrated. Careful consideration must be paid to design and product requirements.









Thin Buffer Layer

Unit: mm

0 Min

Sliding Distance

0.0046061

0.0040303

0.0034546

0.0028788

0.0023031

0.0017273

0.0011515

0 Min

0.00057576

Unit: mm

Time: 2

Time: 2

Type: Sliding Distance 04/04/2017 11:54 0.0051819 Max



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Cassette Level Optimisation

• Cassette level optimisation focuses on stress across the individual IGBT





Chamfer Size (mm

- improve cassette yield and electrical performance.
- Parameterised FEM provides response surface for optimisation.
- Key performance indicators are:
 - Peak Stress
 - Thermal resistance
 - Stress Range

Package Level Optimisation

• Package level optimisation requires consideration of compliance to accommodate component tolerances and providing an effective cooling solution.

Collector

Strain Buffe

Thickness

Chamfer Size

• There are two packaging concepts : 'rigid' and compliant... • Rigid devices offer double side cooling • Compliant devices offer spring constants several orders of magnitude smaller than rigid devices.



- Assuming linear elastic response, in order to have a meaningful con-tribution from the emitter side cooling, pillar geometry the results in a spring constant over 1000N/µm is required
- Given the tolerances of the Press-Pack components the rigid device will experience plastic deformation under clamping load
- Even factoring in plastic deformation, the rigid package cannot meet a compliant designs tolerance for component variations



Conclusions

Development of Press-Pack IGBTs is a multifaceted process. There are three key considerations:

1. Optimising IGBT protection vs reliability.

Sample Data



2. Optimising IGBT stress vs Thermal resistance

3. Optimising Packaging compliance vs thermal resistance.

Points 1 & 2 may be considered by FEM simulation, however, packaging design should be considered on an application basis -

- Compliant designs offer the best switching performance and therefore are required for the highest current ratings
- Rigid Packages are appropriate for small diameter packages e.g. GTO replacements



